CURRICULUM VITAE EXAMPLE

MARK ARNOLD

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EDUCATION:

9/XX-9/XX **Stanford University**, Stanford, California
Ph.D. degree in Materials Science. (June 20XX)

9/XX-6/XX **Cornell University**, Ithaca, New York.
A.B. degree in Physics. Graduation with high honors.
Allen G. Shenstone Prize in Physics, for senior thesis.

DISSERTATION:"Metal Interfaces with III-V Semiconductors".
Advisor: Professor William Jones
Coadvisor: Professor John Smith
This work comprises a surface-science-analytic investigation of Schottky barrier formation and morphology of metal interfaces to GaAs and InP. Most of the dissertation has been published as journal articles (see publication list).

OTHER RESEARCH EXPERIENCE:

4/XX-9/XX **Additional Graduate Research**, Stanford University. In addition to dissertation work, studied resonant photoemission in rare earth metals. Participated in numerous other experiments, including studies of optically enhanced oxidation of GaAs, and of the band structure of InP.

6/XX-12/XX **Research Assistant**, Stanford University (with advisor W. Jones). Assisted with theoretical investigation of the magnetic proximity effect in thin film interfaces; work resulted in publication (see publication list).

9/XX-6/XX **Senior Thesis**, Cornell University. Studied the effects of Zeeman splitting fields in He relating to an ongoing experiment to obtain a new measurement of the Lamb shift in He.

Summers
19XX-XX **Undergraduate Research Assistant**, Cornell University Cyclotron. Work included design and construction of an NMR-based high-precision magnetic field measurement/stabilization instrument for use in an experiment to measure the Lamb shift in He. Evolved into a part of senior thesis.

PUBLICATIONS:
Presented at conferences:

1. M.M. Arnold, W. Jones and J. Smith, "Systematics of metal contacts to GaAs", J. Vac. Sci. Technol. (20XX) (in press).

   Presented at the 20XX Workshop on the Physics and Chemistry of Interface Chemistry.

2. M.M. Arnold, W. Jones and J. Smith, "Ga bonding in metal/GaAs interface formation", J. Vac. Sci. Technol. B3, 980-985 (20XX).

   Presented at the 20XX Conference on the Physics and Chemistry of Semiconductor Interfaces.

3. M.M. Arnold, W. Jones and J. Smith, “The Ag/GaAs and Ag/InP interfaces”, J. Vac. Sci. Technol. A3, 19XX-19XX (19XX).

   Presented at the 19XX Conferences on the Physics and Chemistry of Semiconductor Interfaces.

Other First Author:

4. M.M. Arnold, W. Jones and J. Smith, “Diffusion of Ag at the Ag/InP interface”, Appl. Phys. Lett. 48, 44-46 (20XX).

5. M.M. Arnold, W. Jones and J. Smith, “Effect of different cation-anion bond strengths on metal-ternary-semiconductor interface formation: Au/GaInp”, Phys. Rev. B33, 5329-5342 (20XX).

6. M.M. Arnold, “Overlayer-cation reaction at the Cu/InP interface”, Phys. Rev. B32, 1188-1195 (20XX).

7. M.M. Arnold and W. Jones, “Resonant photoemission at the 5p threshold in La, Pr, Sm and Tb”, J. Electron Spectrosc. Relat. Phenom. 31, 59-66 (19XX).

Coauthor:

1. J.A. Harper, M.M. Arnold, W. Jones, and J. Smith, “Angle-resolved photoemission spectroscopy of GaAs”, J. Vac. Sci. Technol. A4, 233-237 (2001).

2. L.S. Stoneman and M.M. Arnold, “Theory of the magnetic proximity effect”, J. Magn. Mater. 47, 117-123 (2000).